

FIG. 1A

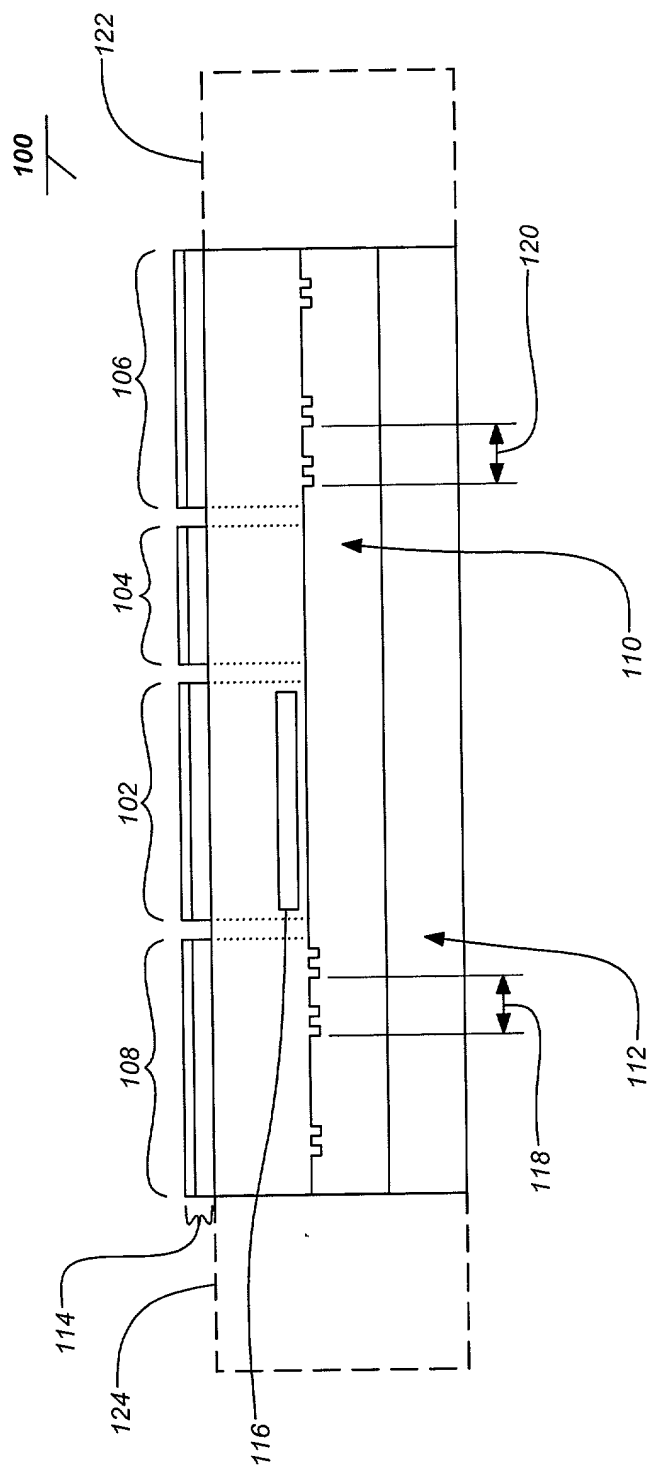


FIG. 1B

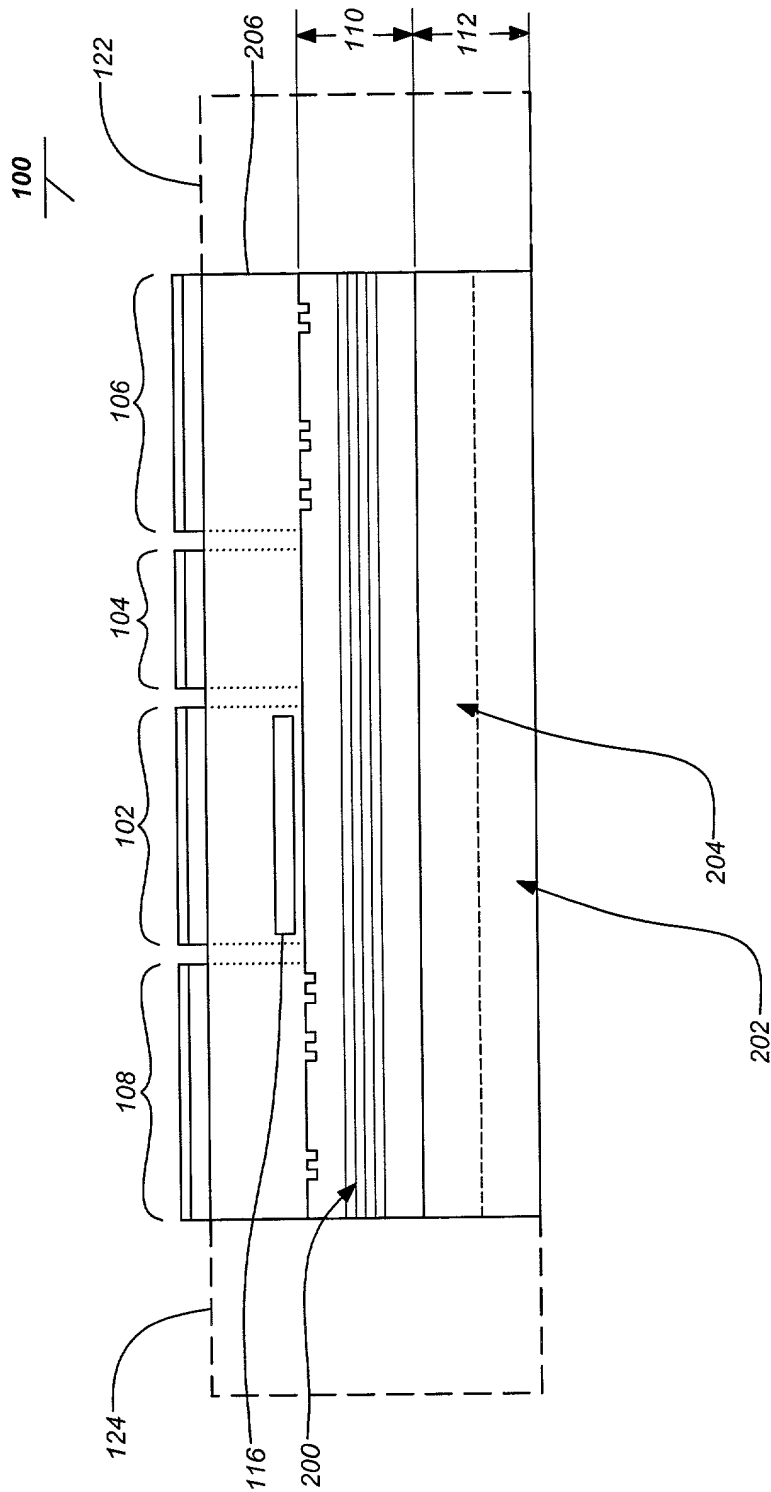


FIG. 2

FIG. 3

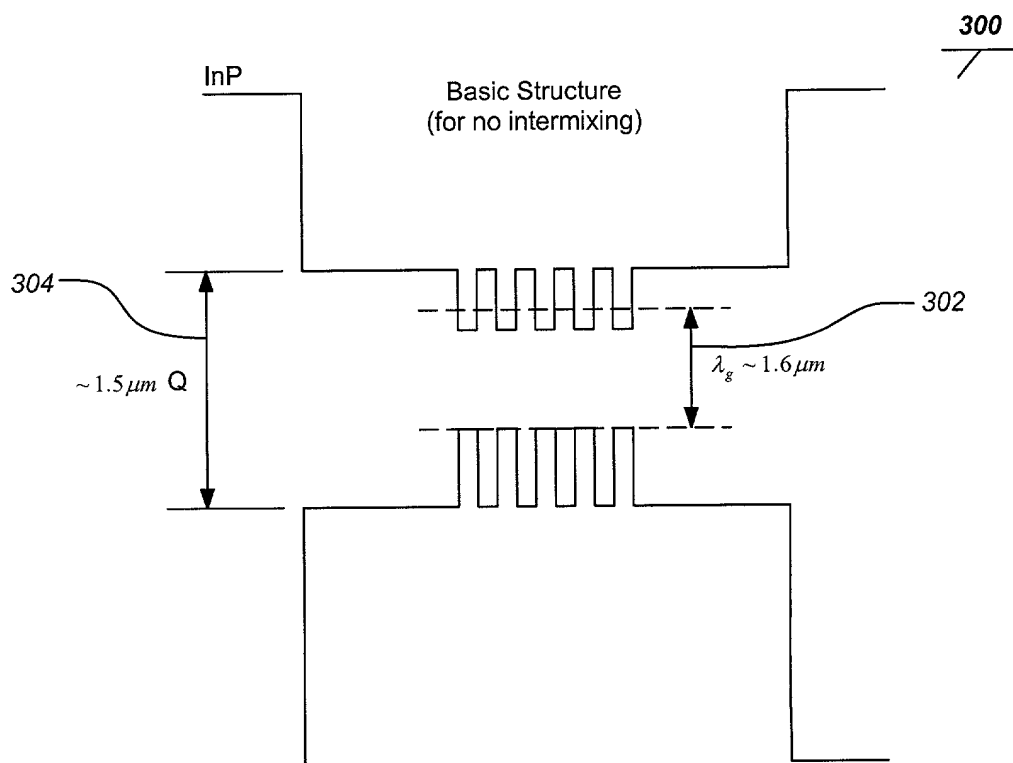


FIG. 3

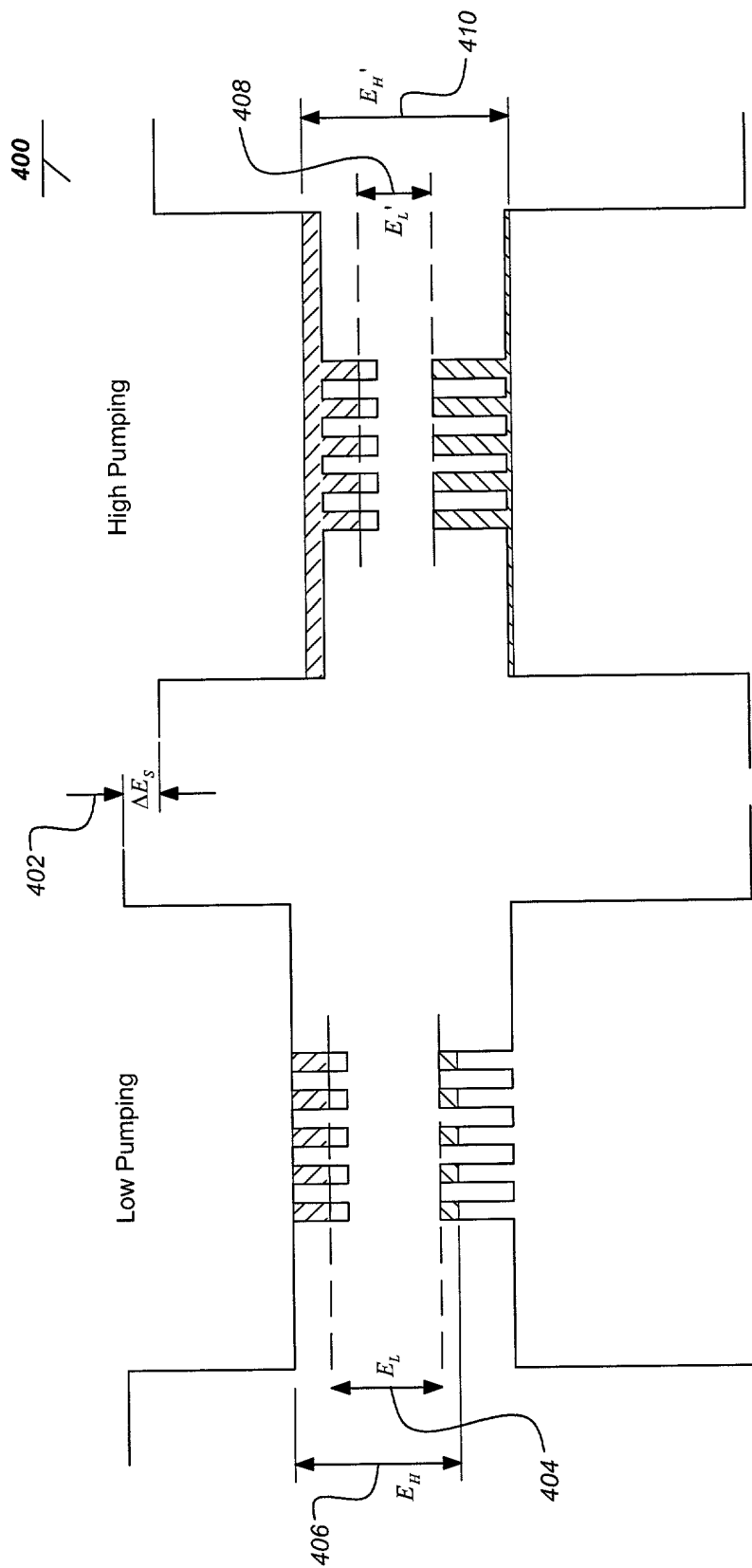


FIG. 4

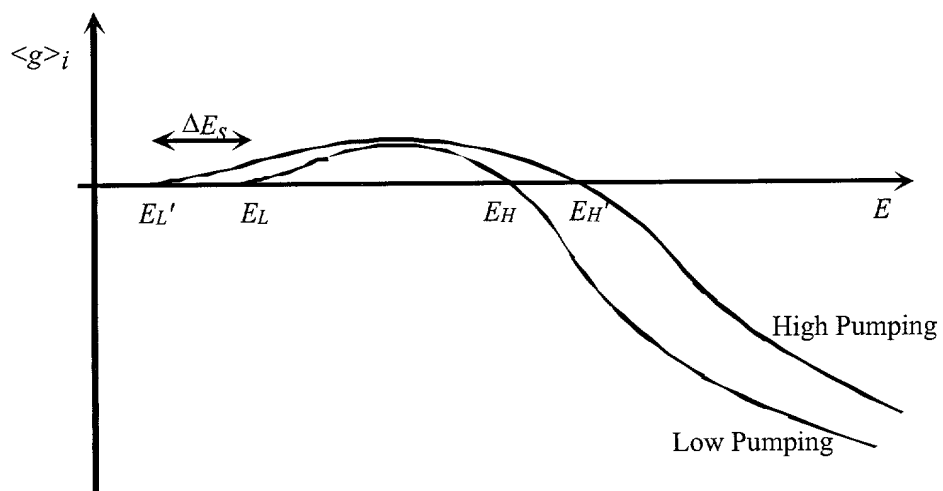


FIG. 5

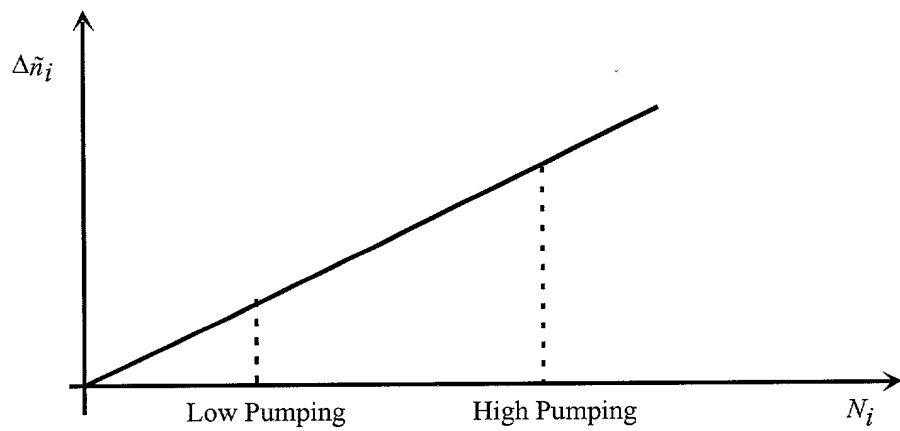


FIG. 6

Intermixed Structure
(Different base structure with higher bandgap SCH)

$\sim 1.45 \mu m Q$

700

702

$\lambda_g \sim 1.48 \mu m$

The diagram shows a cross-section of a semiconductor device. At the top is a layer labeled '700'. Below it is a wavy layer labeled 'Intermixed Structure (Different base structure with higher bandgap SCH)'. Below that is a layer labeled '702'. At the bottom is a large rectangular block. A vertical double-headed arrow indicates the thickness of the '702' layer, labeled $\lambda_g \sim 1.48 \mu m$. A label $\sim 1.45 \mu m Q$ is placed near the interface between the wavy layer and the '702' layer.

FIG. 7

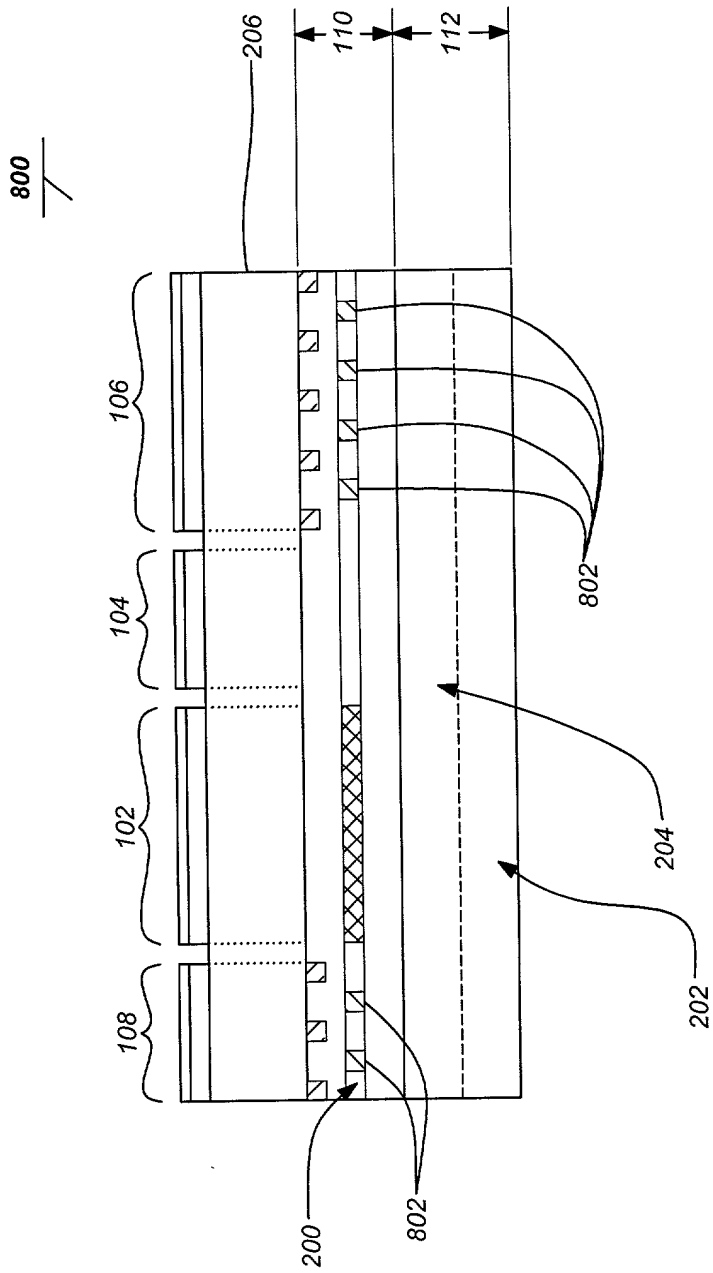


FIG. 8A

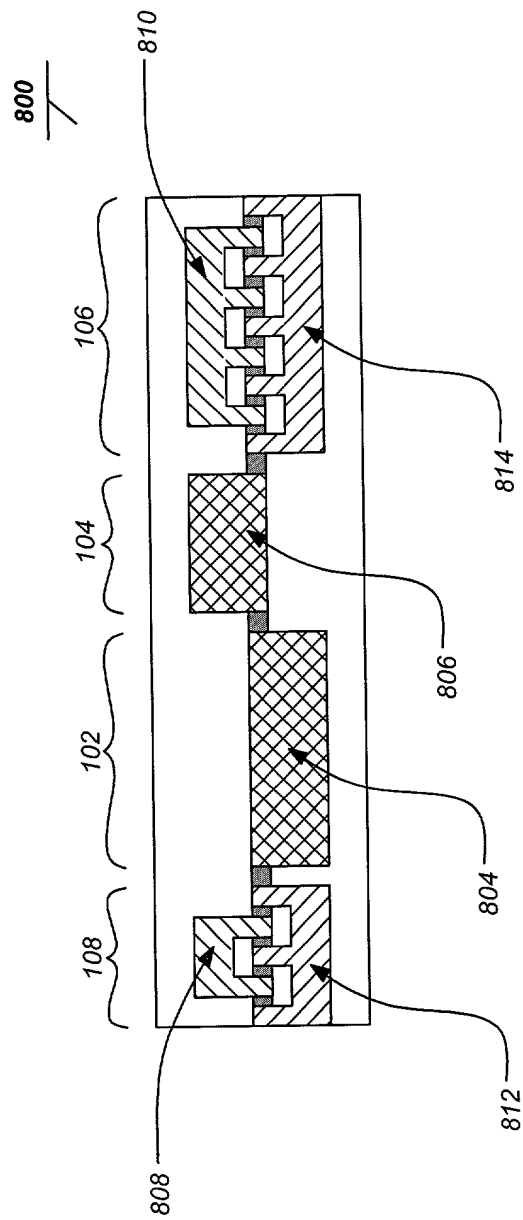


FIG. 8B